Revision 0.91



2017-11-22

TAPERED AMPLIFIERS Semiconductor Optical Amplifier

General Product Information	
Product	Application
808 nm Tapered Amplifier	Spectroscopy
C-Mount Package	Metrology



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Symbol	Unit	min	typ	max
Ts	°C	-40		85
T _C	°C	0		50
I _F	А			3
V _R	V			0
P _{opt}	W			1.1
	T _s T _c I _F V _R	$\begin{array}{c c} T_{S} & \circ C \\ T_{C} & \circ C \\ I_{F} & A \\ V_{R} & V \end{array}$	$\begin{array}{c c} T_{s} & \circ C & -40 \\ T_{c} & \circ C & 0 \\ I_{F} & A \\ V_{R} & V \end{array}$	$\begin{array}{c c} T_{s} & \circ C & -40 \\ T_{c} & \circ C & 0 \\ I_{F} & A \\ V_{R} & V \end{array}$

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	5		40
Forward Current	١ _F	А			2.5
Input Power	P _{input}	mW	10		50
Output Power	P _{opt}	W			1.0

Characteristics at T_{LD} = 25 °C at BOL

Parameter	Symbol	Unit	min	typ	max
Design Wavelength	λ_{C}	nm		808	
Gain Width (FWHM)	Δλ	nm		15	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.3	
Operational Current @ $P_{opt} = 1.0 W$	I _{op Gain}	А			2.5
Output Power	P _{opt}	W	1.0		
Amplification	G	dB		13	
Cavity length	L _C	μm		4000	

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Measurement Conditions / Comments
non condensing
with proper injection from a seed laser

Measurement Conditions / Comments

with proper injection from a seed laser	

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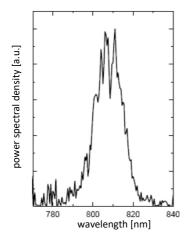
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Characteristics at T_{LD} = 25 °C	Cat BOL				cont'd
Parameter	Symbol	Unit	min	typ	max
Reflectivity at Front Facet	R _{ff}			3.10-4	1.10-3
Reflectivity at Rear Facet	R _{rf}			3.10-4	1.10-3
Input Aperture (at rear side)	d _{in}	μm		3	
Output Aperture (at front side)	d _{out}	μm		290	
Astigmatism	А	μm		640	
Input Divergence parallel (1/e ²)	$\Theta_{\text{in} }$	0			
Input Divergence perpendicular (1/e ²)	$\Theta_{\text{in}\perp}$	0			
Output Divergence parallel (1/e ²)	$\Theta_{out }$	0			
Output Divergence perpendicular (1/e ²)	$\Theta_{\text{out}\perp}$	0			
Polarization				TM	

Typical Measurement Results

spectrum measured w/o injection



depending on operating conditions E field perpendicular to junction plane

Measurement Conditions / Comments

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.







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Symbol	Unit	min	typ	max
h	mm	7.05	7.10	7.20
t	mm		4.05	
		h mm	h mm 7.05	h mm 7.05 7.10

Package Pinout

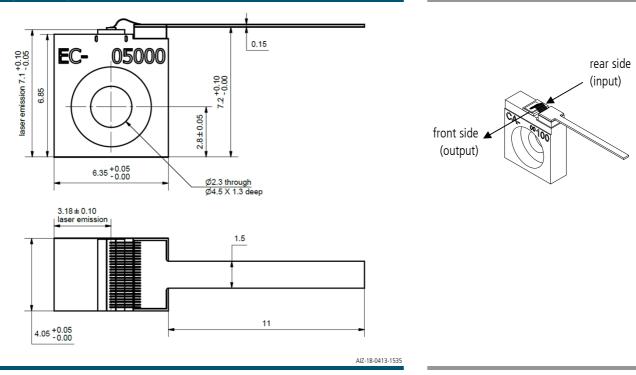
Mounting Wire Housing

Cathode (-) Anode (+)

CA- 00100 (+) heat spreader

Measurement Conditions / Comments

Package Drawings



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Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TPA diode type is known to be sensitive against thermal stress. It should not be operated without appropriate injection from a seed laser. Operating at moderate temperatures on proper heat sinks willl contribute to a long lifetime of the diode. The chip should be protected against moisture. A water vapor content below 5000 ppm is recommended for applications with high reliability requirements.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.







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